

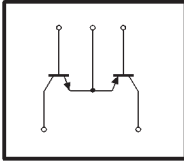
# General purpose (dual transistors)

## FMY5

### ●Features

- Both the 2SA1514K and 2SC3906K chips in an SMT package.
- PNP and NPN chips are connected in a common emitter configuration.

### ●Circuit diagram



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	120	V
Collector-emitter voltage	V <sub>CE0</sub>	120	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>c</sub>	50	mA
Power dissipation	P <sub>c</sub>	300 (TOTAL)	mW *
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

### ●Package, marking, and packaging specifications

Part No.	FMY5
Package	SMT5
Marking	Y5
Code	T148
Basic ordering unit (pieces)	3000

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	120	—	—	V	I <sub>c</sub> =50/-50 μA
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	120	—	—	V	I <sub>c</sub> =1/-1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	5	—	—	V	I <sub>E</sub> =50/-50 μA
Collector cutoff current	I <sub>cbo</sub>	—	—	0.5	μA	V <sub>CB</sub> =100/-100V
Emitter cutoff current	I <sub>EBO</sub>	—	—	0.5	μA	V <sub>EB</sub> =4/-4V
DC current transfer ratio	h <sub>FE</sub>	120	—	820	—	V <sub>CE</sub> =6/-6V, I <sub>c</sub> =2/-2mA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	0.5	V	I <sub>c</sub> =10/-10mA, I <sub>B</sub> =1/-0.1mA
Transition frequency	f <sub>t</sub>	—	140	—	MHz	V <sub>CE</sub> =12/-12V, I <sub>E</sub> =2/-2mA, f=100MHz *
Output capacitance	C <sub>ob</sub>	—	3/4	—	pF	V <sub>CE</sub> =12/-12V, I <sub>E</sub> =0A, f=1MHz

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. \*Transition frequency of the device.

(94S-440-AC41)

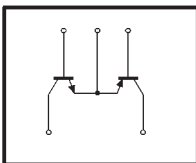
# Totempoles (dual transistors)

## FMY6

### ●Features

- Both the 2SA1036K and 2SC2411K chips in an SMT package.
- PNP and NPN chips are connected in a common emitter configuration.
- High I<sub>Cmax.</sub> (Max. 500mA)

### ●Circuit diagram



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	40	V
Collector-emitter voltage	V <sub>CE0</sub>	32	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>c</sub>	500	mA
Power dissipation	P <sub>d</sub>	300 (TOTAL)	mW *
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

### ●Package, marking, and packaging specifications

Part No.	FMY6
Package	SMT5
Marking	Y6
Code	T148
Basic ordering unit (pieces)	3000

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	40	—	—	V	I <sub>c</sub> =100/-100 μA
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	32	—	—	V	I <sub>c</sub> =1/-1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	5	—	—	V	I <sub>E</sub> =100/-100 μA
Collector cutoff current	I <sub>cbo</sub>	—	—	1	μA	V <sub>CB</sub> =20/-20V
Emitter cutoff current	I <sub>EBO</sub>	—	—	1	μA	V <sub>EB</sub> =4/-4V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	0.4	V	I <sub>c</sub> =100/-100mA, I <sub>B</sub> =10/-10mA
DC current transfer ratio	h <sub>FE</sub>	120	—	—	—	V <sub>CE</sub> /I <sub>c</sub> =3/-3V, I <sub>c</sub> =10/-10mA
Transition frequency	f <sub>t</sub>	—	250/200	—	MHz	V <sub>CE</sub> =5/-5V, I <sub>E</sub> =20/-20mA, f=200MHz *
Output capacitance	C <sub>ob</sub>	—	6.5/7	—	pF	V <sub>CE</sub> =10/-10V, I <sub>E</sub> =0A, f=1MHz

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. \*Transition frequency of mounted transistor.

(96-438-BD11)